

This listing of claims will replace all prior versions,
and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-89 (cancelled)

Claim 90 (new): An active matrix-type liquid crystal display device comprising a pixel electrode and a MOS transistor circuit, the pixel electrode being driven by the MOS transistor circuit, the MOS transistor circuit disposed in the vicinity of a cross-over point of one of a plurality of scanning lines and one of a plurality of signal lines, the MOS type transistor circuit comprising:

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Cmt a first MOS transistor, in which a gate electrode is connected to the scanning line, and one of a source electrode and a drain electrode is connected to the signal line; and

an analog amplifier, in which an input electrode is connected to the other one of the source electrode and the drain electrode of the first MOS transistor and a power supply electrode is connected to the scanning line, and an output electrode is connected to the pixel electrode.

Claim 91 (new): An active matrix-type liquid crystal display device comprising a pixel electrode and a MOS transistor circuit, the pixel electrode being driven by the MOS transistor circuit, the MOS transistor circuit disposed in the vicinity of a cross-over point of one of a plurality of scanning lines and one

of a plurality of signal lines, the MOS type transistor circuit comprising:

a first MOS transistor, in which a gate electrode is connected to the scanning line, and one of a source electrode and a drain electrode is connected to the signal line; and

a second MOS transistor, in which a gate electrode is connected to the other one of the source electrode and the drain electrode of the first MOS transistor, one of a source electrode and a drain electrode is connected to the scanning line, and the other of a source electrode and a drain electrode is connected to the pixel electrode.

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Claim 92 (new): An active matrix-type liquid crystal display device comprising a pixel electrode and a MOS transistor circuit, the pixel electrode being driven by the MOS transistor circuit, the MOS transistor circuit disposed in the vicinity of a cross-over point of one of a plurality of scanning lines and one of a plurality of signal lines, the MOS type transistor circuit comprising:

a first MOS transistor, in which a gate electrode is connected to the scanning line, and one of a source electrode and a drain electrode is connected to the signal line;

a second MOS transistor, in which a gate electrode is connected to the other one of the source electrode and the drain electrode of the first MOS transistor, one of a source electrode

and a drain electrode is connected to the scanning line, and the other one of the source electrode and the drain electrode is connected to the pixel electrode; and a resistor, one of two terminals of which is connected to the pixel electrode.

Claim 93 (new): An active matrix-type liquid crystal display device comprising a pixel electrode and a MOS transistor circuit, the pixel electrode being driven by the MOS transistor circuit, the MOS transistor circuit disposed in the vicinity of a cross-over point of one of a plurality of scanning lines and one of a plurality of signal lines, the MOS type transistor circuit comprising:

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a first MOS transistor, in which a gate electrode is connected to the scanning line, and one of the source electrode or the drain electrode is connected to the signal line;

a second MOS transistor, in which a gate electrode is connected to the other one of the source electrode and the drain electrode of the first MOS transistor, one of a source electrode and a drain electrode is connected to the scanning electrode, and another one of the source electrode and the drain electrode is connected to the pixel electrode; and

a third MOS transistor, in which a drain electrode is connected to the pixel electrode.

Claim 94 (new): An active matrix-type liquid crystal display device according to claim 92, wherein the resistance value of the resistor is set to be less than the value of a resistance component which determines a response time constant of a liquid crystal in a pixel.

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Claim 95 (new): An active matrix-type liquid crystal display device according to claim 93, wherein the resistance value between the source electrode and the drain electrode of the third MOS transistor is set to be less than a value of a resistance component which determines a response time constant of a liquid crystal in a pixel.

Claim 96 (new): A method of driving the active matrix-type liquid crystal display device according to claim 90, the method comprising the steps of:

in a scanning line selection period, storing a data signal in the input electrode of the analog amplifier through the first MOS transistor by a scanning

pulse signal and resetting the analog amplifier by use of the scanning pulse signal; and

after completion of the scanning line selection period, writing signals corresponding to the stored data signal to the pixel electrode through the analog amplifier.

Claim 97 (new): A method of driving the active matrix-type liquid crystal display device according to claim 93, the method comprising the steps of:

in a scanning line selection period, storing the data signal in the gate electrode of the second MOS transistor by a scanning pulse signal through the first MOS transistor and resetting the second MOS transistor by transmitting the scanning pulse signal to the pixel electrode through the scanning MOS transistor; and

after completion of the scanning line selection period, writing signals corresponding to the stored data to the pixel electrode through the second MOS transistor, the resistor, or the third MOS transistor.

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Claim 98 (new): An active matrix-type liquid crystal display device comprising a pixel electrode and a MOS transistor circuit, the pixel electrode being driven by the MOS transistor circuit, the MOS transistor circuit disposed in the vicinity of a cross-over point of a plurality of scanning lines and a plurality of signal lines, the MOS type transistor circuit comprising:

a first MOS transistor, in which a gate electrode is connected to an Nth scanning line, N being an integer of 2 or more, and one of a source electrode and a drain electrode is connected to the signal line; and

an analog amplifier, in which a gate electrode is connected to the other one of the source electrode and the drain electrode of the first MOS transistor, one of the source electrode and a drain electrode is connected to an (N-1)th scanning line, and the other one of the source electrode and the drain electrode is connected to the pixel electrode.

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Claim 99 (new): An active matrix-type liquid crystal display device comprising pixel electrodes and MOS transistor circuits, the pixel electrode being driven by the MOS transistor circuit, the MOS transistor circuit disposed in the vicinity of a cross-over point of one of a plurality of scanning lines and one of a plurality of signal lines, the MOS type transistor circuit comprising:

a first MOS transistor, in which a gate electrode is connected to an Nth scanning line, N being an integer of 2 or more, and one of a source electrode and a drain electrode is connected to the signal line; and

a second electrode, in which a gate electrode is connected to the other one of the source electrode and the drain electrode of the first MOS transistor and one of a source electrode and a drain electrode is connected to a (N-1)th scanning line, and the other one of the source electrode and the drain electrode is connected to the pixel electrode.

Claim 100 (new): An active matrix-type liquid crystal display device comprising a pixel electrode and a MOS transistor circuit, the pixel electrode being driven by the MOS transistor circuit, the MOS transistor circuit disposed in the vicinity of a cross-over point of one of a plurality of scanning lines and one of a plurality of signal lines, the MOS type transistor circuit comprising:

a first MOS transistor, in which a gate electrode is connected to an Nth scanning line, N being an integer of 2 or more, and one of a source electrode and a drain electrode is connected to the signal line;

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a second electrode, in which a gate electrode is connected to the other one of the source electrode and the drain electrode of the first MOS transistor and one of a source electrode and a drain electrode is connected to a (N-1)th scanning line, and the other one of the source electrode and the drain electrode is connected to the pixel electrode; and

a resistor, in which one end of two terminals is connected to the pixel electrode.

Claim 101 (new): An active matrix-type liquid crystal display device comprising a pixel electrode and MOS transistor circuits, the pixel electrode driven by the MOS transistor circuit, the MOS transistor circuit disposed in the vicinity of a cross-over point of one of a plurality of scanning lines and one

of a plurality of signal lines, the MOS type transistor circuit comprising:

a first MOS transistor, in which a gate electrode is connected to an Nth scanning line, N being an integer of 2 or more, and one of a source electrode and a drain electrode is connected to the signal line;

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a third MOS transistor, in which a drain electrode is connected to the pixel electrode.

Claim 102 (new): An active matrix-type liquid crystal display device according to claim 100, wherein the resistance value of the resistor is set to be less than a value of a resistance component which determines a response time constant of a liquid crystal in a pixel.

Claim 103 (new): An active matrix-type liquid crystal display device according to claim 101, wherein a resistance value between the source electrode and the drain electrode of the third MOS transistor is set to be less than a value of a resistance

component which determines a response time constant of a liquid crystal in a pixel.

Claim 104 (new): A method of driving the active matrix-type liquid crystal display device according to claim 98 comprising the steps of:

in the (N-1)th scanning line selection period, resetting the analog amplifier by use of the (N-1)th scanning pulse signal;

in the Nth scanning line selection period, storing a data signal in the input electrode of the analog amplifier by the Nth scanning pulse signal through the first MOS transistor; and

after completion of the Nth scanning line selection period, writing signals corresponding to the stored data to the pixel electrode through the analog amplifier.

Claim 105 (new): A method of driving the active matrix-type liquid crystal display device according to claim 101, comprising the steps of:

in the (N-1)th scanning line selection period, resetting the second MOS transistor by transmitting the (N-1)th scanning pulse signal to the pixel electrode through the second MOS transistor;

in the Nth scanning line selection period, storing a data signal in the second MOS transistor by the Nth scanning pulse signal through the first MOS transistor; and

after completion of the Nth scanning line selection period, writing signals corresponding to the stored data to the pixel electrode through the analog amplifier, the resistor, or the third MOS transistor.

Claim 106 (new): An active matrix-type liquid crystal display device according to claim 90, wherein the MOS transistor circuit is formed by integrating thin film transistors.

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Claim 107 (new): An active matrix-type liquid crystal display device according to claim 91, wherein the MOS transistor circuit is formed by integrating thin film transistors.

Claim 108 (new): An active matrix-type liquid crystal display device according to claim 92, wherein the MOS transistor circuit is formed by integrating thin film transistors.

Claim 109 (new): An active matrix-type liquid crystal display device according to claim 93, wherein the MOS transistor circuit is formed by integrating thin film transistors.
